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NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI BAM120** is Designed to operate in a collector modulated VHF Power Amplifier Applications up to 150 MHz.

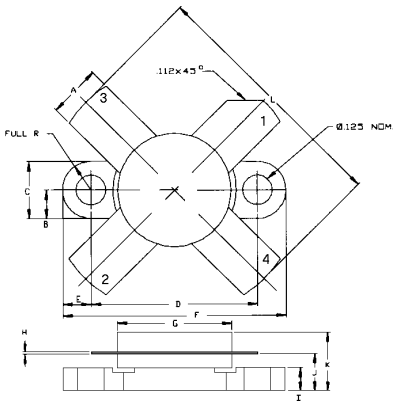
FEATURES:

- η_C = 65 % typ. @ 120 W/150 MHz
- P_G = 9.0 dB typ. @ 120 W/150 MHz
- ***Omnigold***™ Metalization System

MAXIMUM RATINGS

I_C	12 A
V_{CES}	60 V
V_{EBO}	4.0 V
P_{DISS}	140 W @ T_C = 25 °C
T_J	-65 °C to +200 °C
T_{STG}	-65 °C to +150 °C
θ_{JC}	1.2 °C/W

PACKAGE STYLE .500 4L FLG



	MINIMUM Inches/mm	MAXIMUM Inches/mm
A	.220/5,59	.230/5,84
B	.125/3,18	
C	.245/6,22	.255/6,48
D	.720/18,28	.730/18,54
E	.125/3,18	
F	.970/24,64	.980/24,89
G	.495/12,57	.505/12,83
H	.003/0,08	.007/0,18
I	.090/2,29	.110/2,79
J	.160/4,06	.175/4,45
K		.280/7,11
L		1.050/26,67

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1 = COLLECTOR 2 = BASE

3 & 4 = EMITTER

ORDER CODE: ASI10430

CHARACTERISTICS T_C = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CES}	I_C = 20 mA	60			V
BV_{CEO}	I_C = 50 mA	32			V
BV_{EBO}	I_E = 5.0 mA	4.0			V
h_{FE}	V_{CE} = 25 V I_C = 3.5 A	15		100	---
C_{OB}	V_{CE} = 27 V f = 1.0 MHz		240		pF
P_G	V_{CC} = 27 V P_{OUT} = 120 W f = 150 MHz		9.0		dB
η_C			65		%

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Specifications are subject to change without notice.

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